风光欣技术资料

BC860

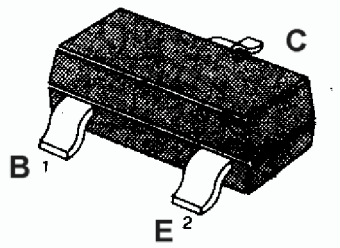
—PNP silicon—

APPLICATION： General purpose applications.

MAXIMUM RATINGS（Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-45	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-100	mA
Collector Power Dissipation	P_C	310	mW
Junction Temperature	T_J	150	℃
Storage Temperature Range	Tstg	－55~150	℃

SOT-23



1.Base 2.Emitter 3.Collector

ELECTRICAL CHARACTERISTICS （Ta=25℃）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	110		800		V_{CE}= -5 V，Ic= -2mA
Collector Cut-off Current	I_{CBO}			-0.015	μA	V_{CB}= -30V，I_E=0
Emitter Cut-off Current	I_{EBO}			-0.015	μA	V_{EB}= -4V，Ic=0
Collector-Base Breakdown Voltage	BV_{CBO}	-50			V	Ic= -0.1mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	-45			V	Ic= -1 mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	-5			V	I_E= -0.1mA，Ic=0
Base-Emitter Voltage	V_{BE}			-0.75	V	V_{CE}= -5V，Ic= -2 mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.3	V	Ic= -100mA，I_B= -0.5mA
				-0.65		Ic= -100 mA，I_B= -5 mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.7		V	Ic= -100 mA，I_B= -0.5 mA
			-0.9			Ic= -100 mA，I_B= -5 mA
Gain bandwidth product	f_T		300		MHz	Ic=-10mA，V_{CE}=-5V, f =100MHz
Common Base Output Capacitance	Cob			6	PF	V_{CB}= -10V，I_E=0，f = 1 MHz
Noise Figure	N_F		1.2	4	dB	V_{CE}= -5 V,Ic= -0.2 mA,f= 1 kHz, Rg= 2kΩ

h_{FE} **Classification And Marking**

Print Mark	9BA	9BB	9BC
Classification	A	B	C
h_{FE}	110~220	200~450	420~800